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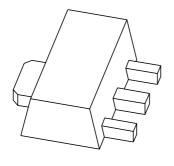
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BST50; BST51; BST52 NPN Darlington transistors

Product data sheet Supersedes data of 2001 Feb 20

2004 Dec 09



NPN Darlington transistors

BST50; **BST51**; **BST52**

FEATURES

- High current (max. 0.5 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

APPLICATIONS

- Industrial switching applications such as:
 - Print hammer
 - Solenoid
 - Relay and lamp driving.

DESCRIPTION

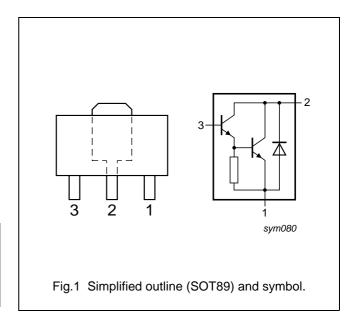
NPN Darlington transistor in a SOT89 plastic package. PNP complements: BST60, BST61 and BST62.

MARKING

TYPE NUMBER	MARKING CODE
BST50	AS1
BST51	AS2
BST52	AS3

PINNING

PIN	DESCRIPTION	
1	emitter	
2	collector	
3	base	



ORDERING INFORMATION

TYPE NUMBER	PACKAGE			
TIPE NOMBER	NAME	E DESCRIPTION V		
BST50	SC-62	plastic surface mounted package; collector pad for good heat	SOT89	
BST51		transfer; 3 leads		
BST52				

NPN Darlington transistors

BST50; BST51; BST52

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BST50		_	60	V
	BST51		_	80	V
	BST52		_	90	V
V _{CES}	collector-emitter voltage	V _{BE} = 0 V			
	BST50		_	45	V
	BST51		_	60	V
	BST52		_	80	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	1	Α
I _{CM}	peak collector current		_	2	Α
I _B	base current (DC)		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	1.3	W
Tj	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	96	K/W
$R_{th(j-s)}$	thermal resistance from junction to soldering point		16	K/W

Note

Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm².
 For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

^{1.} Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm². For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

NPN Darlington transistors

BST50; BST51; BST52

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CES}	collector-emitter cut-off current					
	BST50	V _{BE} = 0 V; V _{CE} = 45 V	_	_	50	nA
	BST51	V _{BE} = 0 V; V _{CE} = 60 V	_	_	50	nA
	BST52	V _{BE} = 0 V; V _{CE} = 80 V	_	_	50	nA
I _{EBO}	emitter-base cut-off current	I _C = 0 A; V _{EB} = 4 V	_	_	50	nA
h _{FE}	DC current gain	V _{CE} = 10 V; note 1; (see Fig.2)				
		I _C = 150 mA	1000	_	_	
		I _C = 500 mA	2000	_	_	
V _{CEsat}	collector-emitter saturation	$I_C = 500 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	1.3	V
	voltage	$I_C = 500 \text{ mA}; I_B = 0.5 \text{ mA};$ $T_j = 150 \text{ °C}$	_	_	1.3	V
V _{BEsat}	base-emitter saturation voltage	$I_C = 500 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	1.9	V
f _T	transition frequency	$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V};$ f = 100 MHz	-	200	-	MHz
Switching ti	Switching times (between 10% and 90% levels); (see Fig.3)					
t _{on}	turn-on time	I _{Con} = 500 mA; I _{Bon} = 0.5 mA;	_	400	_	ns
t _{off}	turn-off time	$I_{Boff} = -0.5 \text{ mA}$	_	1500	_	ns

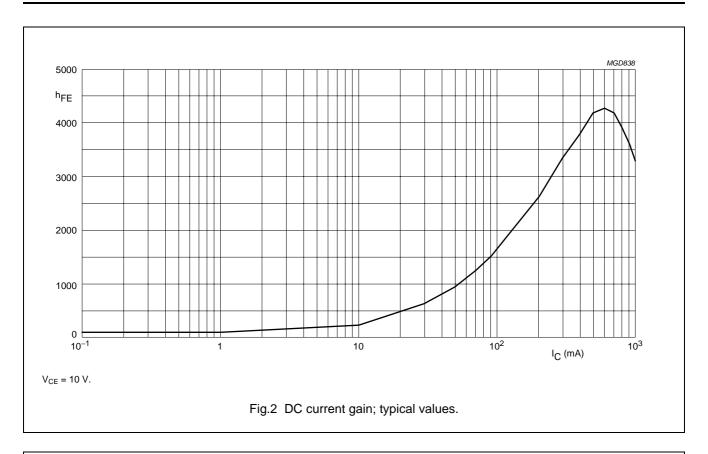
Note

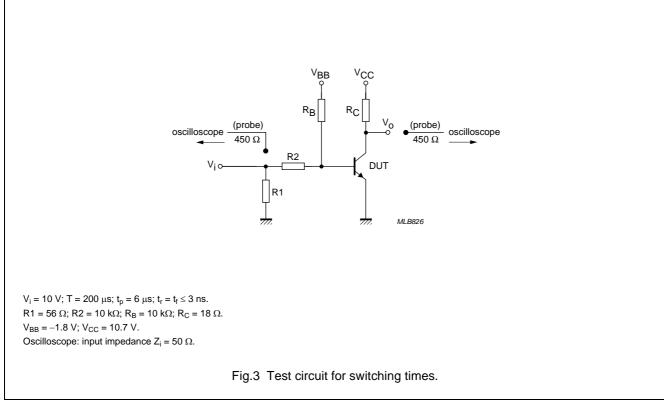
1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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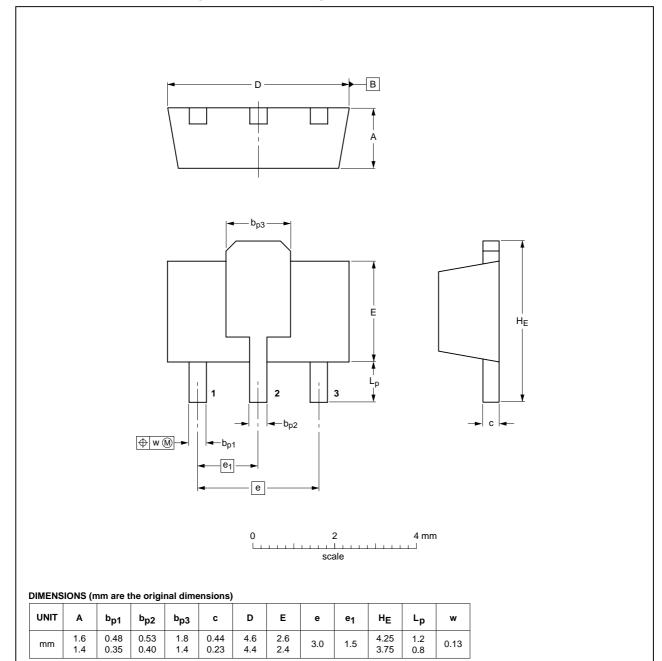
NPN Darlington transistors

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PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION ISSUE DATE	
SOT89		TO-243	SC-62			04-08-03 06-03-16

NPN Darlington transistors

BST50; BST51; BST52

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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Printed in The Netherlands R75/05/pp8 Date of release: 2004 Dec 09 Document order number: 9397 750 13877

